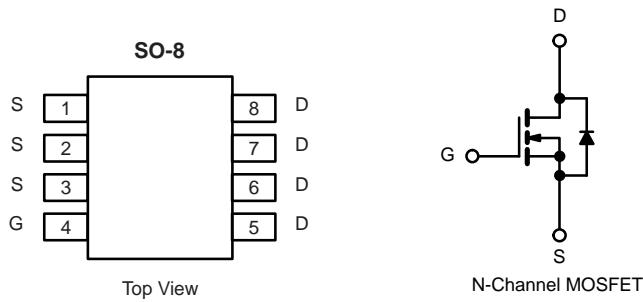


N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
100	0.020 at $V_{GS} = 10$ V	10.4	23 nC
	0.027 at $V_{GS} = 8$ V	9.5	

FEATURES

- Halogen-free According to IEC 61249-2-21
- Definition
- Extremely Low Q_{gd} for Switching Losses
- 100 % R_g Tested
- 100 % Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Primary Side Switch

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C)	I_D	10.4	A	
		9.1		
		8.5 ^{b, c}		
		7.5 ^{b, c}		
Pulsed Drain Current	I_{DM}	50		
Continuous Source-Drain Diode Current	I_S	4.5	A	
		2.6 ^{b, c}		
Single Pulse Avalanche Current	I_{AS}	20	mJ	
Single Pulse Avalanche Energy	E_{AS}	20		
Maximum Power Dissipation	P_D	5.9	W	
		3.8		
		3.1 ^{b, c}		
		2 ^{b, c}		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	33	40	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 80 °C/W.

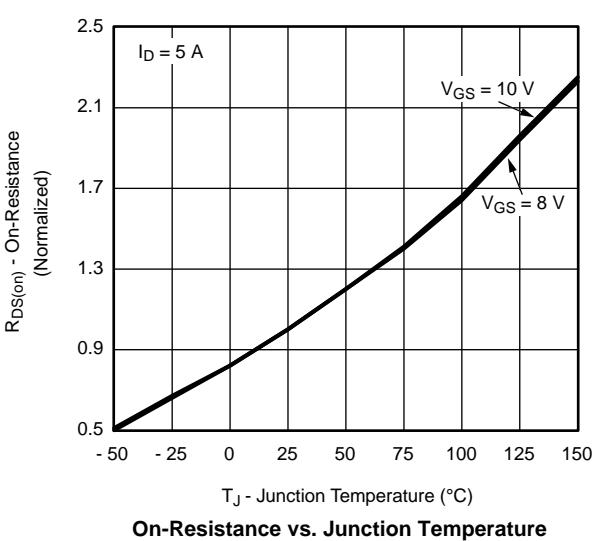
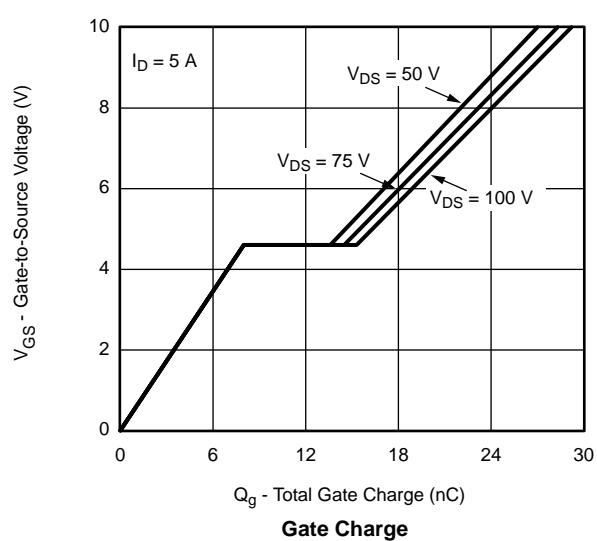
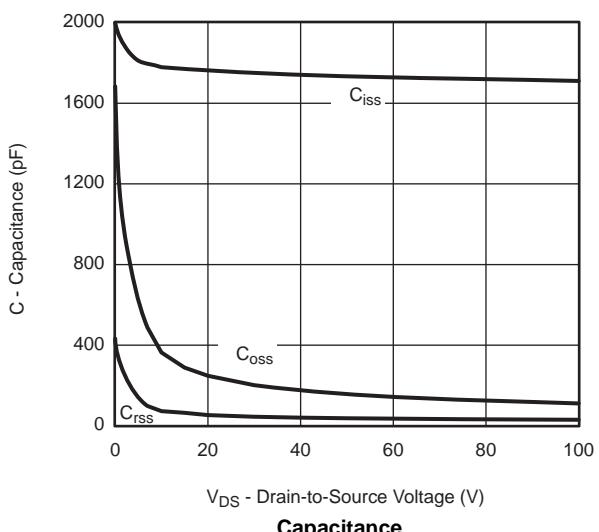
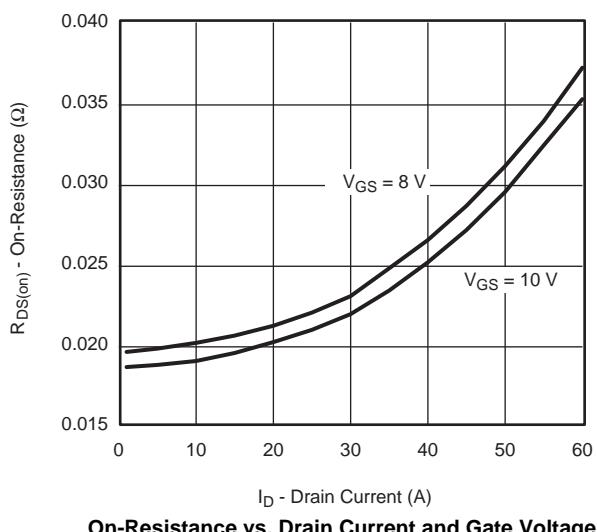
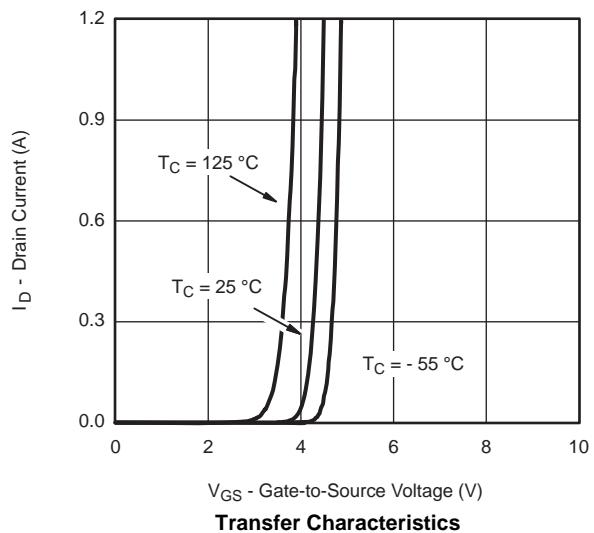
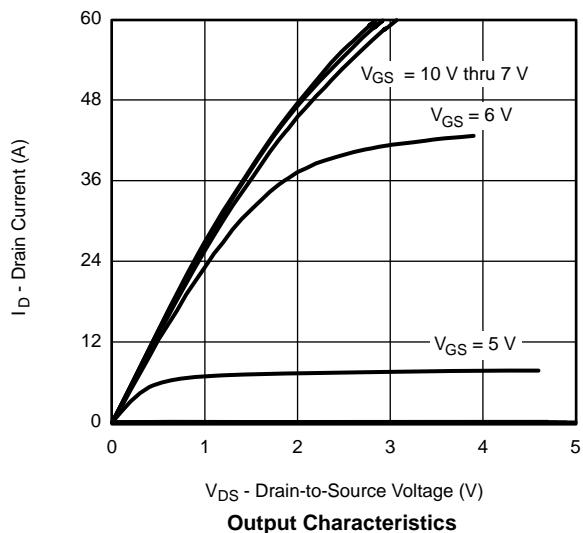
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

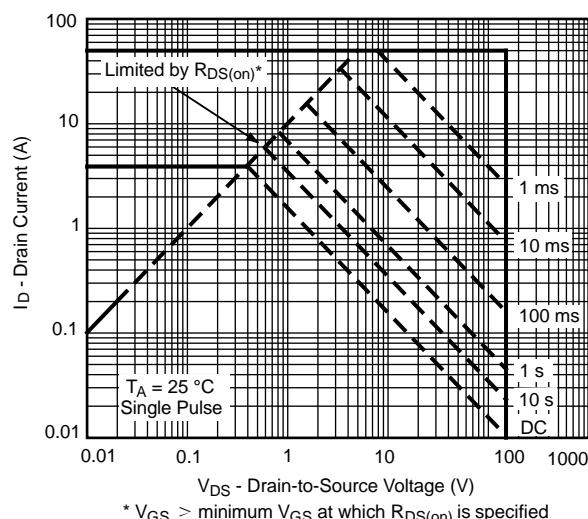
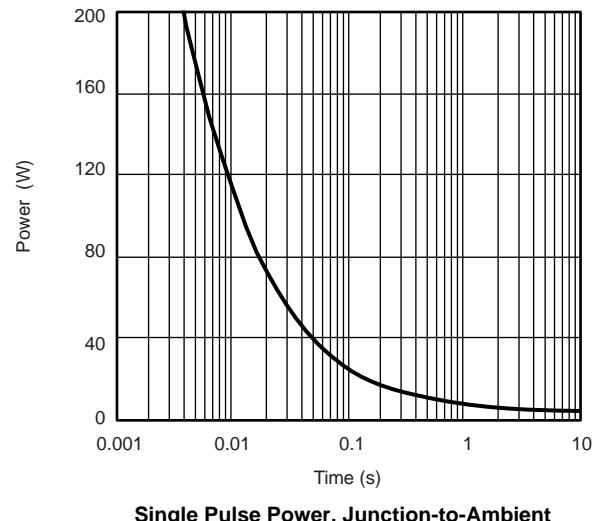
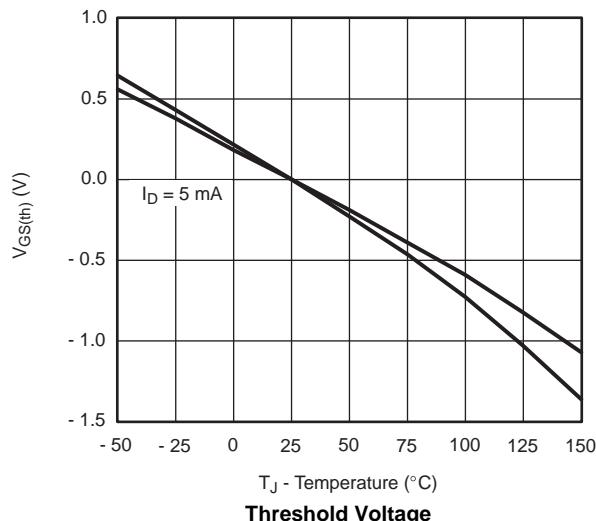
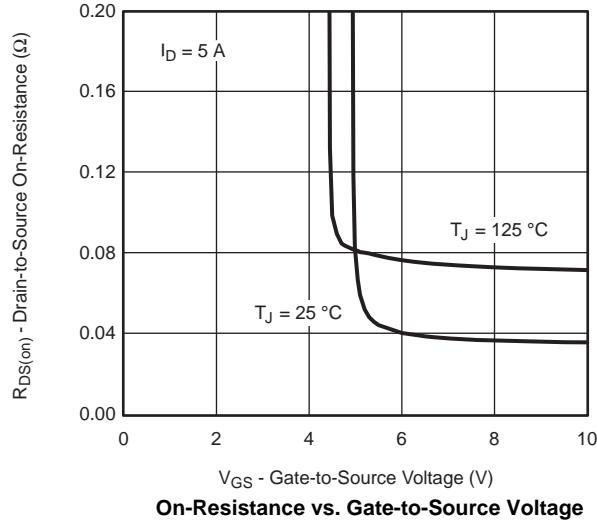
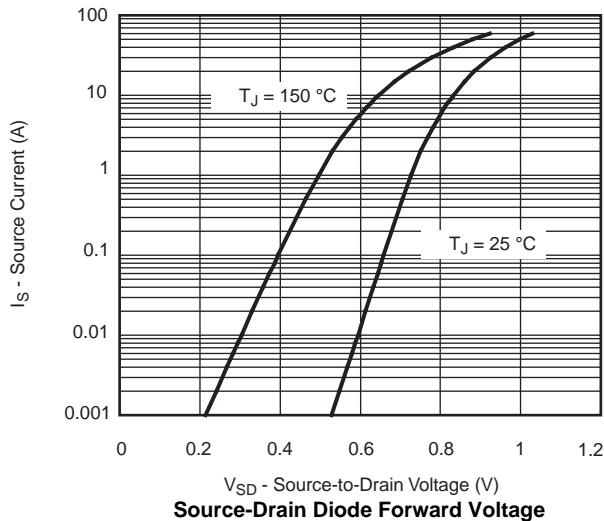
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		172		
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 10		$\text{mV}/^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	1.5		4.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	
		$V_{DS} = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			10	μA
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 10 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$		0.020		
		$V_{GS} = 8 \text{ V}$, $I_D = 5 \text{ A}$		0.027		Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 5 \text{ A}$		23		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1735		
Output Capacitance	C_{oss}			160		pF
Reverse Transfer Capacitance	C_{rss}			37		
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$		28.5	43	nC
				23	35	
Gate-Source Charge	Q_{gs}	$V_{DS} = 75 \text{ V}$, $V_{GS} = 8 \text{ V}$, $I_D = 5 \text{ A}$		8		
Gate-Drain Charge	Q_{gd}			6.5		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		0.85	1.3	Ω
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{DD} = 50 \text{ V}$, $R_L = 10 \Omega$ $I_D \equiv 5 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		14	21	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(\text{off})}$			22	33	
Fall Time	t_f			6	10	
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 50 \text{ V}$, $R_L = 10 \Omega$ $I_D \equiv 5 \text{ A}$, $V_{GEN} = 8 \text{ V}$, $R_g = 1 \Omega$		16	24	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(\text{off})}$			20	30	
Fall Time	t_f			7	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			7.7	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 2.6 \text{ A}$		0.77	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 5 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		63	95	ns
Body Diode Reverse Recovery Charge	Q_{rr}			110	165	nC
Reverse Recovery Fall Time	t_a			49		ns
Reverse Recovery Rise Time	t_b			14		

Notes:

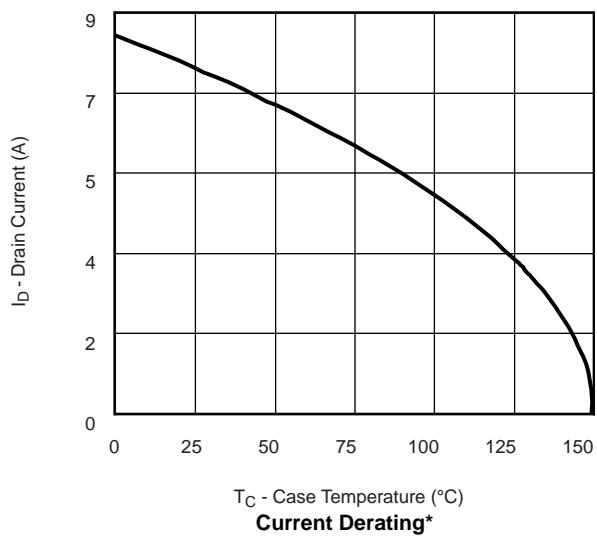
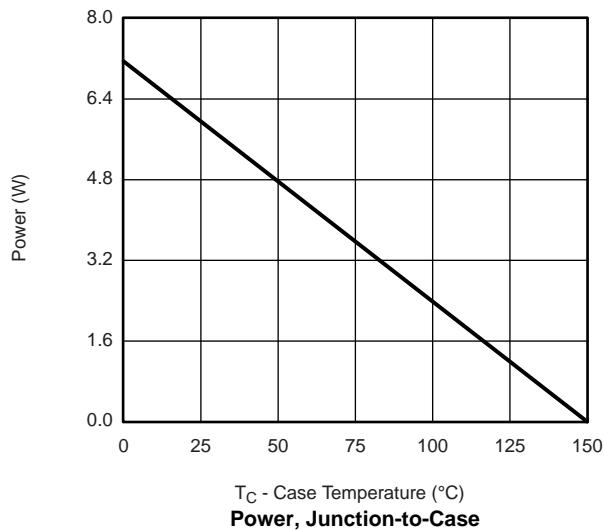
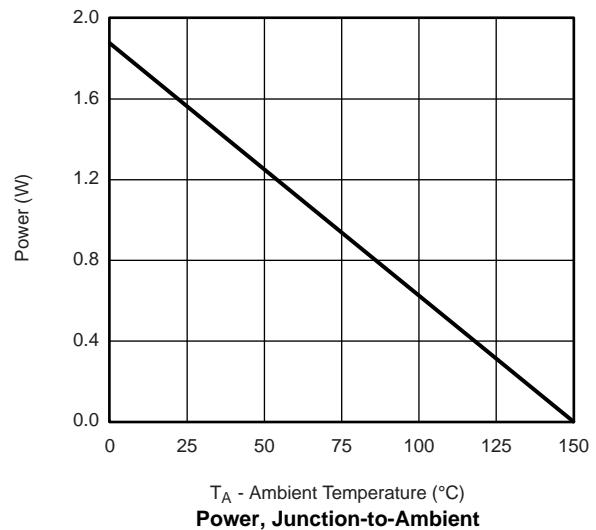
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
- a. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

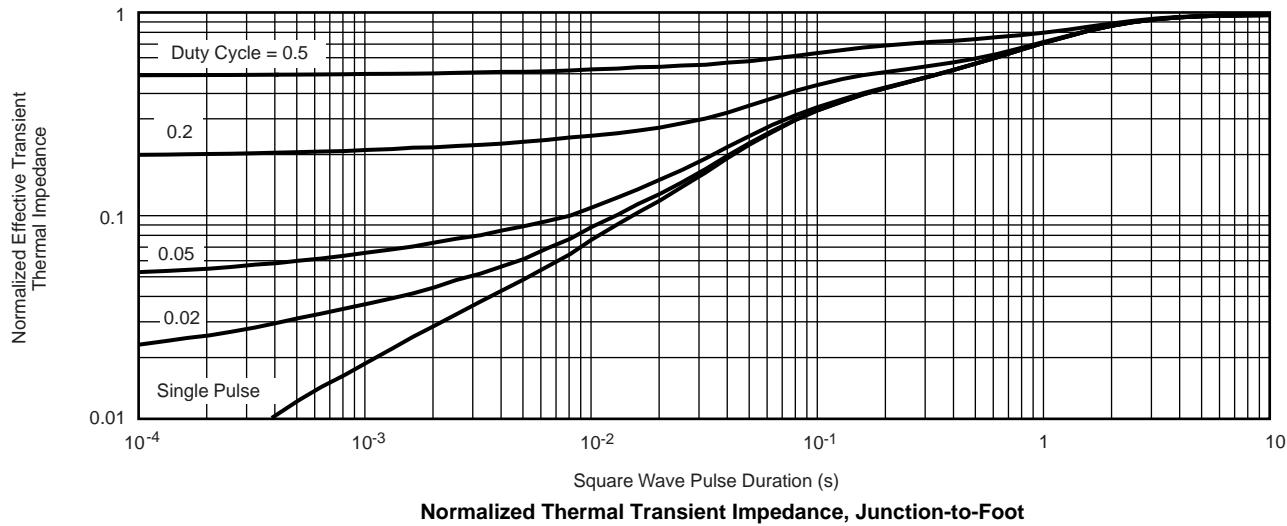
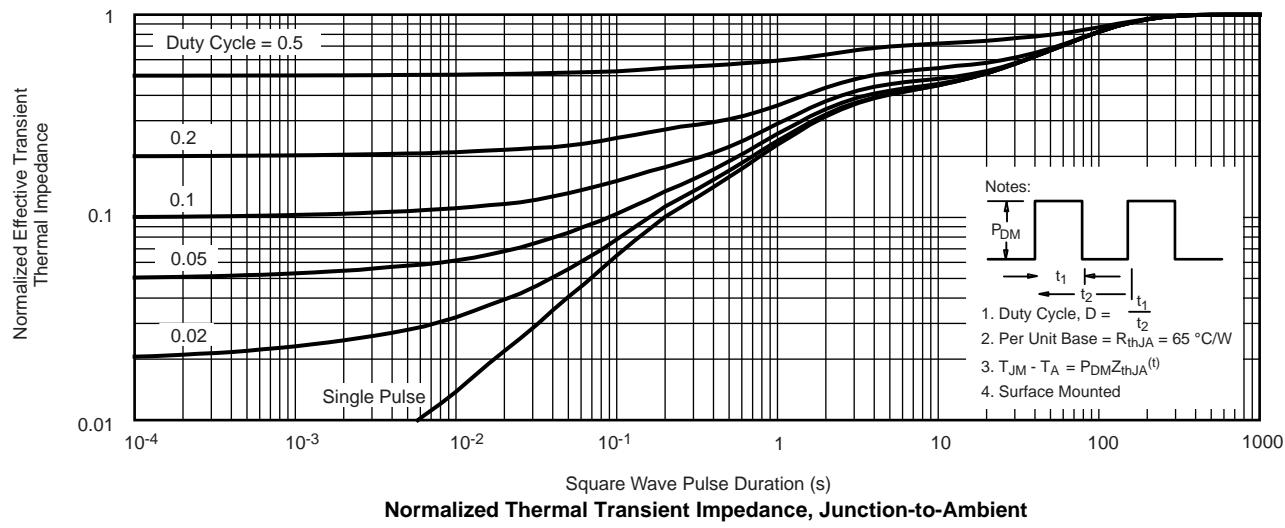
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


* $V_{GS} > \text{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

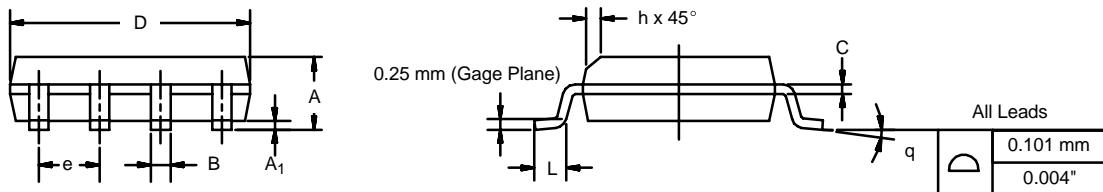
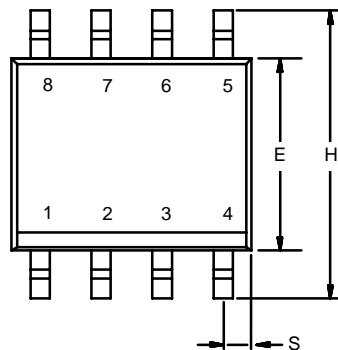
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Case

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


SOIC (NARROW): 8-LEAD

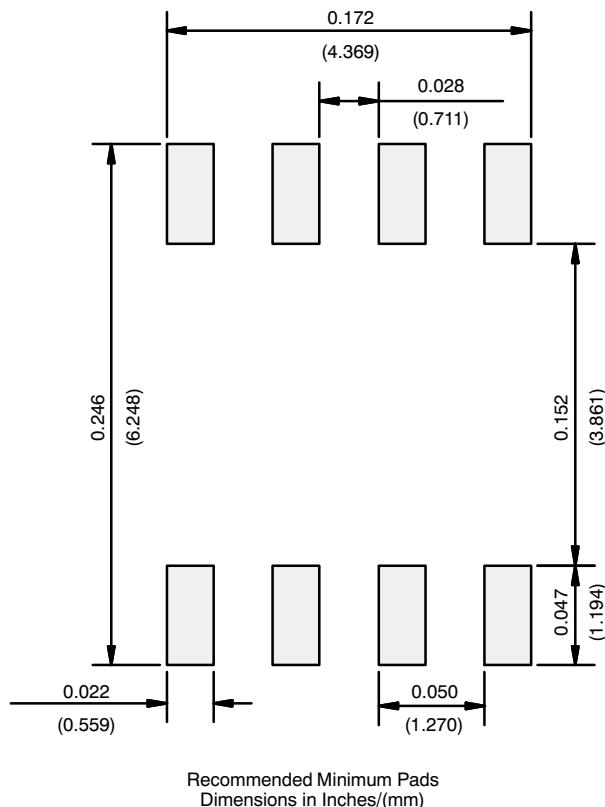
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

ECN: C-06527-Rev. I, 11-Sep-06
 DWG: 5498

RECOMMENDED MINIMUM PADS FOR SO-8



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